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Amorphous Si/SiO₂ distributed Bragg reflectors with transfer printed single-crystalline Si nanomembranes

Minkyu Cho, Jung-Hun Seo, Deyin Zhao, Jaeseong Lee, Kanglin Xiong, Xin Yin, Yonghao Liu, Shih-Chia Liu, Munho Kim, Tong J. Kim, Xudong Wang, Weidong Zhou and Zhenqiang Ma
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V-band monolithic microwave integrated circuit with continuous wave output power of >23.5 dBm using conventional AlGaIn/GaN-on-Si structure

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S **Classical momentum gap for electron transport in vacuum and consequences for space charge in thermionic converters with a grid electrode**

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Temperature-dependent electrical instability of p-type SnO thin-film transistors

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S **Gold-free contacts on Al_xGa_{1-x}N/GaN high electron mobility transistor structure grown on a 200-mm diameter Si(111) substrate**

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S **Influence of ZnSe capping of CdSe layers in the growth mode of ZnCdMgSe/CdSe/ZnCdMgSe heterostructures**

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High aspect ratio and large area metallic nanogrids as transparent electrodes on optoelectronic devices

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Nearly lattice-matched $\text{Zn}_{1-z}\text{Cd}_z\text{Se}/\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{Zn}_{1-y}\text{Mg}_y\text{Se}$ ($z > x$) quantum wells for yellow emission

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Keigo Kasuya, Souichi Katagiri and Takashi Ohshima
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S **Thermally stable device isolation by inert gas heavy ion implantation in AlGaIn/GaN HEMTs on Si**

Subramaniam Arulkumaran, Kumud Ranjan, Geok Ing Ng, John Kennedy, Peter P. Murmu, Thirumaleshwara N. Bhat and Sudhiranjan Tripathy
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S **SiO₂ nanohole arrays with high aspect ratio for InGaIn/GaN nanorod-based phosphor-free white light-emitting-diodes**

Wantae Lim, Hyun Kum, Young-Jin Choi, Sung-Hyun Sim, Ji-Hye Yeon, Jung-Sub Kim, Han-Kyu Seong, Nam-Goo Cha, Yong-Il Kim, Young-Soo Park, Geonwook Yoo and Stephen J. Pearton
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Magnetoreflexion spectroscopy of monolayer transition-metal dichalcogenide semiconductors in pulsed magnetic fields

Andreas V. Stier, Kathleen M. McCreary, Berend T. Jonker, Junichiro Kono and Scott A. Crooker
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Core–shell carrier and exciton transfer in GaAs/GaNAs coaxial nanowires

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S **Thickness characterization of atomically thin WSe₂ on epitaxial graphene by low-energy electron reflectivity oscillations**

Sergio C. de la Barrera, Yu-Chuan Lin, Sarah M. Eichfeld, Joshua A. Robinson, Qin Gao, Michael Widom and Randall M. Feenstra
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S **Correlation between structural order parameter of epitaxial Fe/Pt multilayer and corresponding perpendicular magnetic anisotropy and orbital magnetic moment upon annealing**

Yu-Sheng Chen, Chih-Hao Lee and Hong-Ji Lin
J. Vac. Sci. Technol. B **34**, 04J109 (2016);
<http://dx.doi.org/10.1116/1.4955132>

+ VIEW DESCRIPTION

S **Nanoscale Schottky barrier mapping of thermally evaporated and sputter deposited W/Si(001) diodes using ballistic electron emission microscopy**

Westly Nolting, Chris Durcan, Avyaya J. Narasimham and Vincent P. LaBella
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<http://dx.doi.org/10.1116/1.4958721>

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S **Reduced efficiency droop of nonpolar a-plane (11-20) GaN-based light-emitting diodes by vertical injection geometry**

Min Joo Park, Seung Kyu Oh, Tak Jeong, Sukkoo Jung and Joon Seop Kwak
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<http://dx.doi.org/10.1116/1.4958720>

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